

INSULATED GATE BIPOLAR TRANSISTOR WITH  
 ULTRAFAST SOFT RECOVERY DIODE

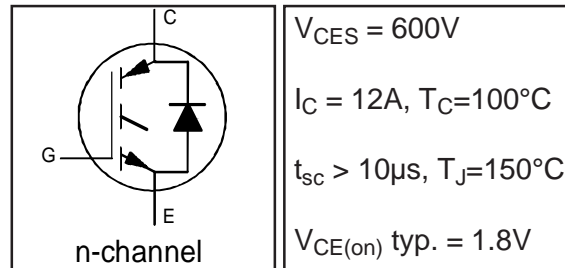
IRGB10B60KD  
 IRGS10B60KD  
 IRGSL10B60KD

**Features**

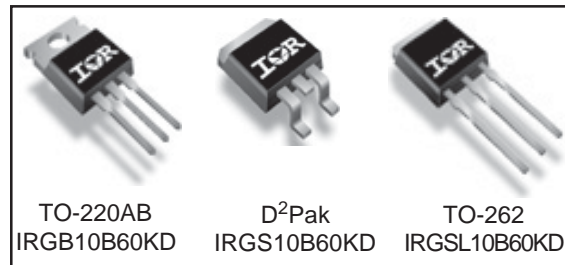
- Low VCE (on) Non Punch Through IGBT Technology.
- Low Diode VF.
- 10µs Short Circuit Capability.
- Square RBSOA.
- Ultrasoft Diode Reverse Recovery Characteristics.
- Positive VCE (on) Temperature Coefficient.

**Benefits**

- Benchmark Efficiency for Motor Control.
- Rugged Transient Performance.
- Low EMI.
- Excellent Current Sharing in Parallel Operation.



$V_{CES} = 600V$   
 $I_C = 12A, T_C = 100^\circ C$   
 $t_{sc} > 10\mu s, T_J = 150^\circ C$   
 $V_{CE(on)} \text{ typ.} = 1.8V$



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	22	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	12	
$I_{CM}$	Pulsed Collector Current	44	
$I_{LM}$	Clamped Inductive Load Current ④	44	
$I_F @ T_C = 25^\circ C$	Diode Continuous Forward Current	22	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	10	
$I_{FM}$	Diode Maximum Forward Current	44	
$V_{GE}$	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	156	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	62	
$T_J$	Operating Junction and	-55 to +150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

**Thermal Resistance**

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	0.8	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	3.4	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount①	—	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady state)②	—	—	40	
Wt	Weight	—	1.44	—	g

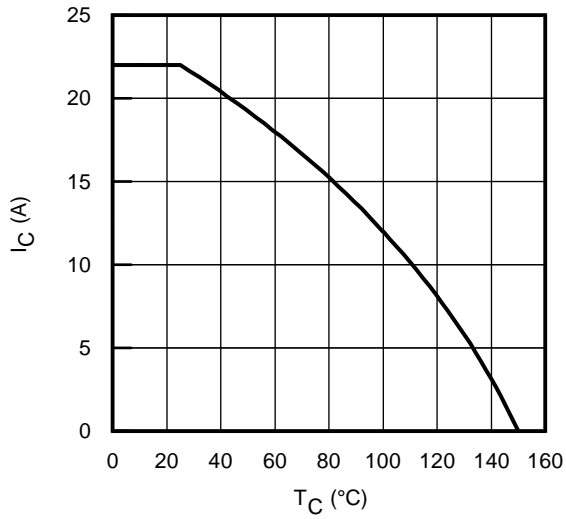
## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
V <sub>(BR)CES</sub>	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V <sub>GE</sub> = 0V, I <sub>C</sub> = 500μA	
ΔV <sub>(BR)CES</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Breakdown Voltage	—	0.3	—	V/°C	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1.0mA, (25°C-150°C)	
V <sub>CE(on)</sub>	Collector-to-Emitter Saturation Voltage	1.5	1.80	2.20	V	I <sub>C</sub> = 10A, V <sub>GE</sub> = 15V	5, 6,7
		—	2.20	2.50		I <sub>C</sub> = 10A, V <sub>GE</sub> = 15V T <sub>J</sub> = 150°C	9,10,11
V <sub>GE(th)</sub>	Gate Threshold Voltage	3.5	4.5	5.5	V	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250μA	9,10,11
ΔV <sub>GE(th)</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/°C	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 1.0mA, (25°C-150°C)	12
g <sub>fe</sub>	Forward Transconductance	—	7.0	—	S	V <sub>CE</sub> = 50V, I <sub>C</sub> = 10A, PW=80μs	
I <sub>CES</sub>	Zero Gate Voltage Collector Current	—	3.0	150	μA	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V	
		—	300	700		V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V, T <sub>J</sub> = 150°C	
V <sub>FM</sub>	Diode Forward Voltage Drop	—	1.30	1.45	V	I <sub>C</sub> = 10A	8
		—	1.30	1.45		I <sub>C</sub> = 10A T <sub>J</sub> = 150°C	
I <sub>GES</sub>	Gate-to-Emitter Leakage Current	—	—	±100	nA	V <sub>GE</sub> = ±20V	

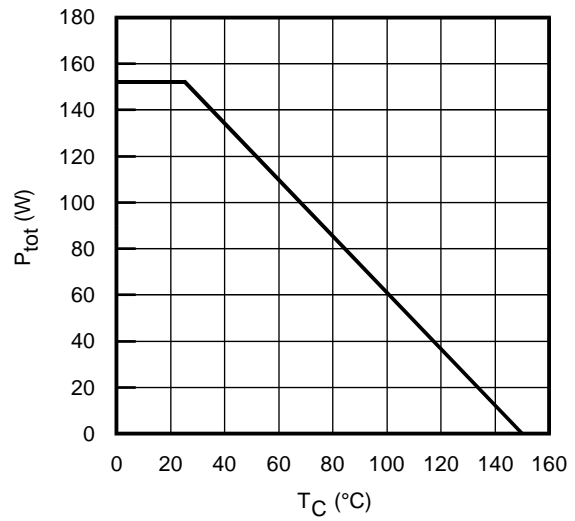
## Switching Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
Q <sub>g</sub>	Total Gate Charge (turn-on)	—	38	—	nC	I <sub>C</sub> = 10A	CT1
Q <sub>ge</sub>	Gate - Emitter Charge (turn-on)	—	4.3	—		V <sub>CC</sub> = 400V	
Q <sub>gc</sub>	Gate - Collector Charge (turn-on)	—	16.3	—		V <sub>GE</sub> = 15V	
E <sub>on</sub>	Turn-On Switching Loss	—	140	247	μJ	I <sub>C</sub> = 10A, V <sub>CC</sub> = 400V	CT4
E <sub>off</sub>	Turn-Off Switching Loss	—	250	360		V <sub>GE</sub> = 15V, R <sub>G</sub> = 47Ω, L = 200μH	
E <sub>tot</sub>	Total Switching Loss	—	390	607		L <sub>s</sub> = 150nH T <sub>J</sub> = 25°C ③	
t <sub>d(on)</sub>	Turn-On Delay Time	—	30	39	ns	I <sub>C</sub> = 10A, V <sub>CC</sub> = 400V	CT4
t <sub>r</sub>	Rise Time	—	20	29		V <sub>GE</sub> = 15V, R <sub>G</sub> = 47Ω, L = 200μH	
t <sub>d(off)</sub>	Turn-Off Delay Time	—	230	262		L <sub>s</sub> = 150nH, T <sub>J</sub> = 25°C	
t <sub>f</sub>	Fall Time	—	23	32			
E <sub>on</sub>	Turn-On Switching Loss	—	230	340	μJ	I <sub>C</sub> = 10A, V <sub>CC</sub> = 400V	CT4
E <sub>off</sub>	Turn-Off Switching Loss	—	350	464		V <sub>GE</sub> = 15V, R <sub>G</sub> = 47Ω, L = 200μH	
E <sub>tot</sub>	Total Switching Loss	—	580	804		L <sub>s</sub> = 150nH T <sub>J</sub> = 150°C ③	
t <sub>d(on)</sub>	Turn-On Delay Time	—	30	39	ns	I <sub>C</sub> = 10A, V <sub>CC</sub> = 400V	14, 16
t <sub>r</sub>	Rise Time	—	20	28		V <sub>GE</sub> = 15V, R <sub>G</sub> = 47Ω, L = 200μH	
t <sub>d(off)</sub>	Turn-Off Delay Time	—	250	274		L <sub>s</sub> = 150nH, T <sub>J</sub> = 150°C	
t <sub>f</sub>	Fall Time	—	26	34			
C <sub>ies</sub>	Input Capacitance	—	620	—	pF	V <sub>GE</sub> = 0V	
C <sub>oes</sub>	Output Capacitance	—	62	—		V <sub>CC</sub> = 30V	
C <sub>res</sub>	Reverse Transfer Capacitance	—	22	—		f = 1.0MHz	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T <sub>J</sub> = 150°C, I <sub>C</sub> = 44A, V <sub>p</sub> = 600V V <sub>CC</sub> = 500V, V <sub>GE</sub> = +15V to 0V, R <sub>G</sub> = 47Ω	4 CT2
SCSOA	Short Circuit Safe Operating Area	10	—	—	μs	T <sub>J</sub> = 150°C, V <sub>p</sub> = 600V, R <sub>G</sub> = 47Ω V <sub>CC</sub> = 360V, V <sub>GE</sub> = +15V to 0V	CT3 WF4
E <sub>rec</sub>	Reverse Recovery energy of the diode	—	245	330	μJ	T <sub>J</sub> = 150°C	17,18,19
t <sub>rr</sub>	Diode Reverse Recovery time	—	90	105	ns	V <sub>CC</sub> = 400V, I <sub>F</sub> = 10A, L = 200μH	20, 21
I <sub>rr</sub>	Diode Peak Reverse Recovery Current	—	19	22	A	V <sub>GE</sub> = 15V, R <sub>G</sub> = 47Ω, L <sub>s</sub> = 150nH	CT4, WF3

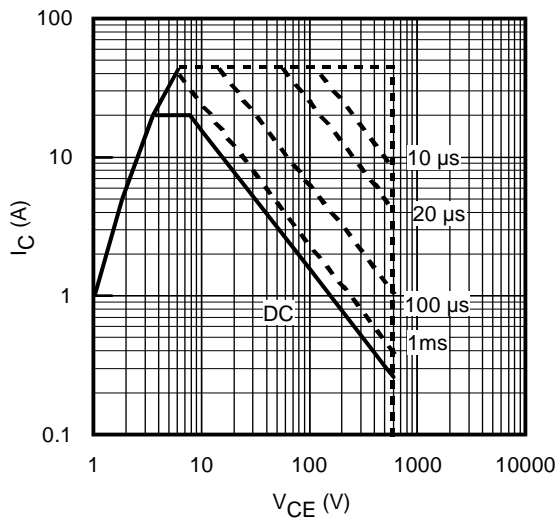
Note ① to ④ are on page 15



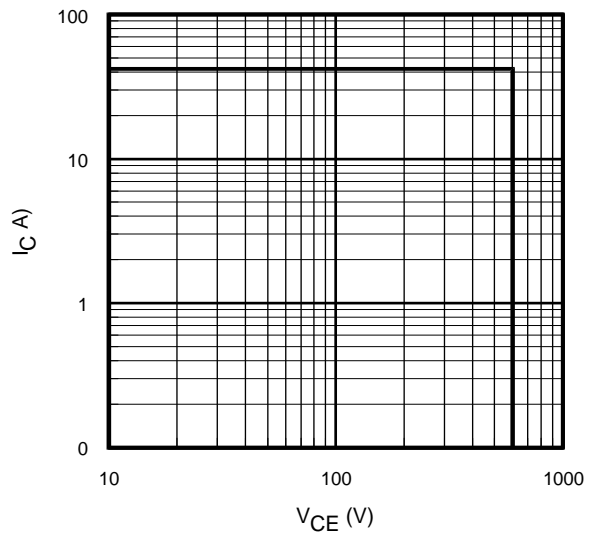
**Fig. 1** - Maximum DC Collector Current vs. Case Temperature



**Fig. 2** - Power Dissipation vs. Case Temperature

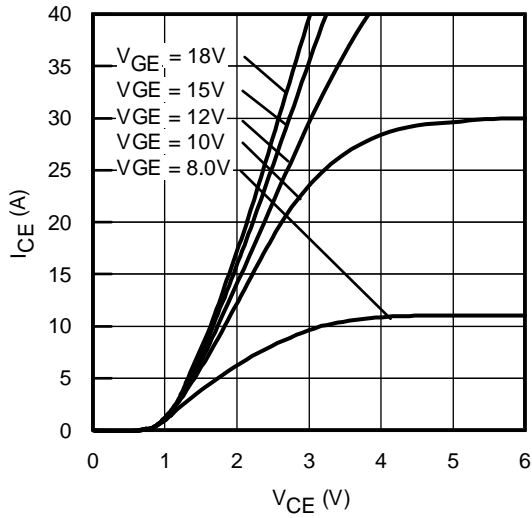


**Fig. 3** - Forward SOA  
 $T_C = 25^\circ\text{C}$ ;  $T_J \leq 150^\circ\text{C}$

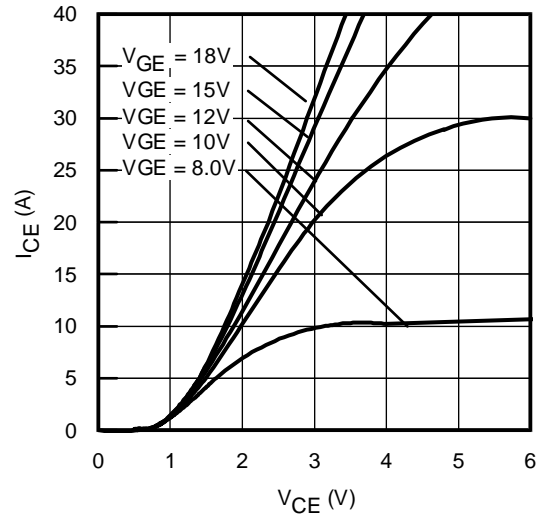


**Fig. 4** - Reverse Bias SOA  
 $T_J = 150^\circ\text{C}$ ;  $V_{GE} = 15\text{V}$

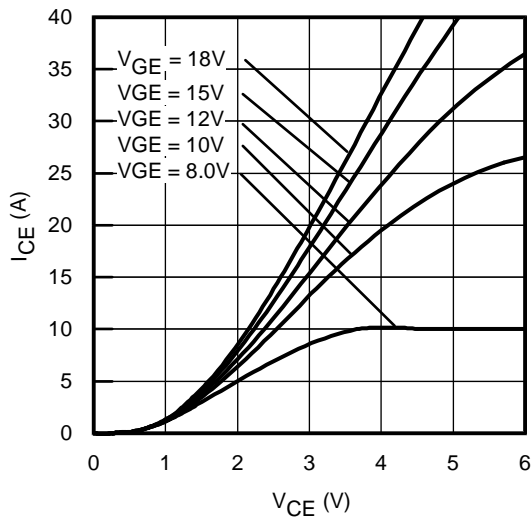
# IRG/B/S/SL10B60KD



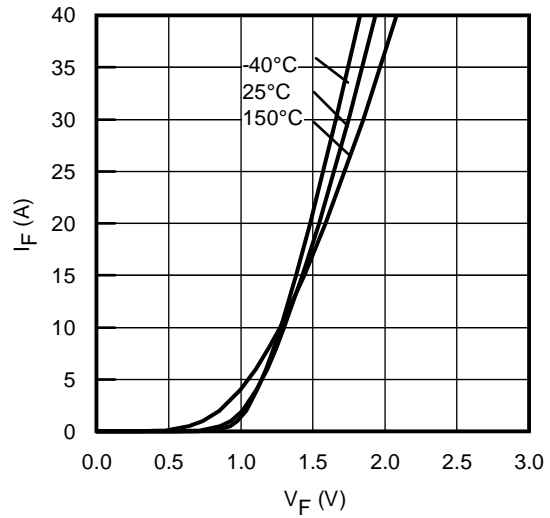
**Fig. 5** - Typ. IGBT Output Characteristics  
 $T_J = -40^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



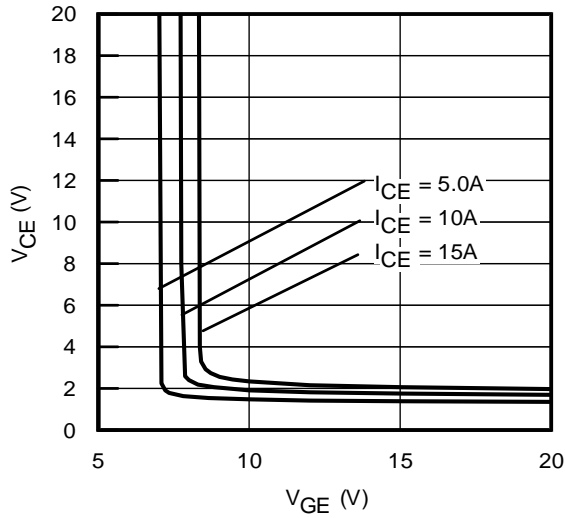
**Fig. 6** - Typ. IGBT Output Characteristics  
 $T_J = 25^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



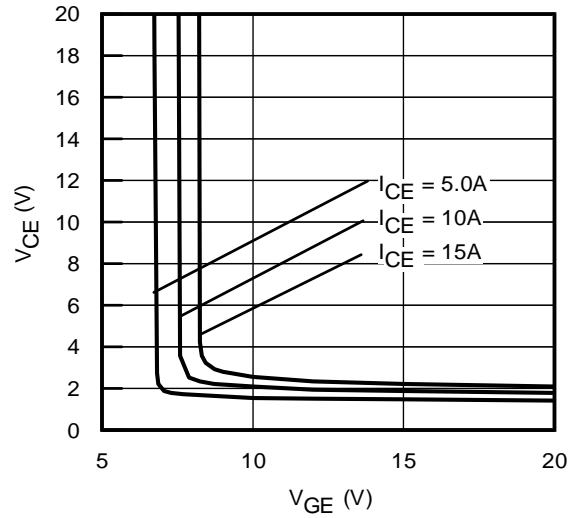
**Fig. 7** - Typ. IGBT Output Characteristics  
 $T_J = 150^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



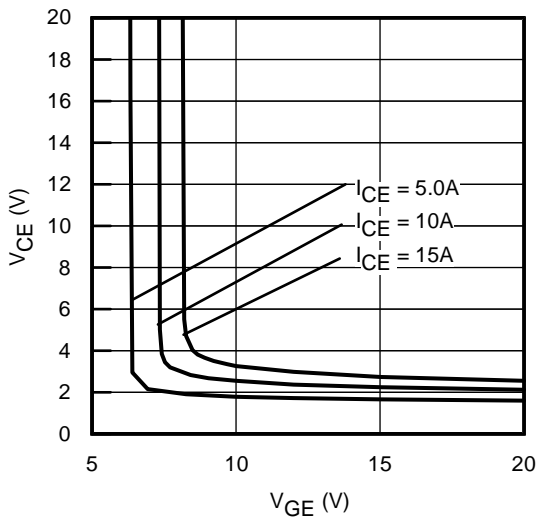
**Fig. 8** - Typ. Diode Forward Characteristics  
 $t_p = 80\mu\text{s}$



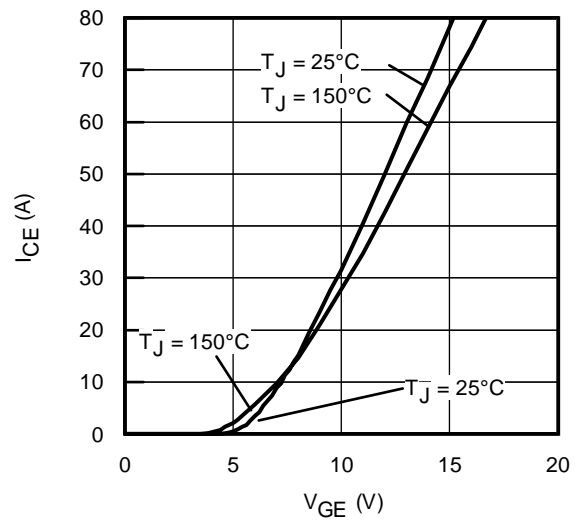
**Fig. 9** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = -40^\circ\text{C}$



**Fig. 10** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 25^\circ\text{C}$

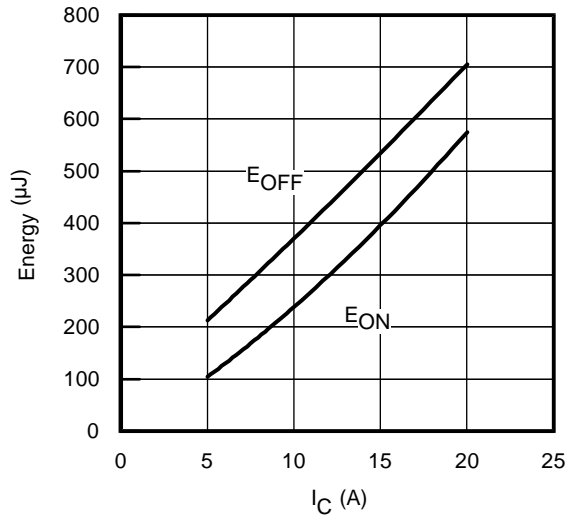


**Fig. 11** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 150^\circ\text{C}$

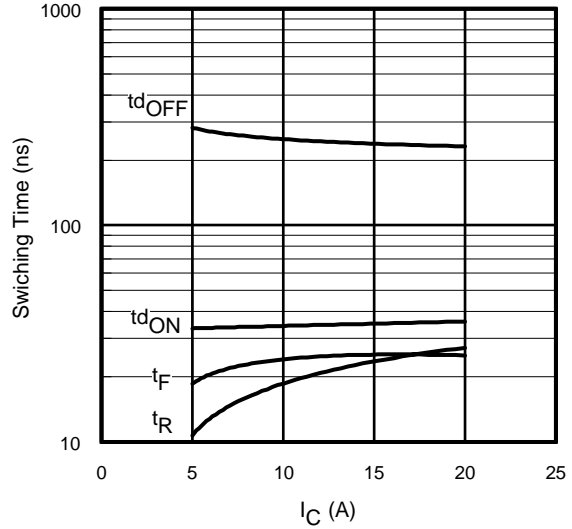


**Fig. 12** - Typ. Transfer Characteristics  
 $V_{CE} = 50\text{V}$ ;  $t_p = 10\mu\text{s}$

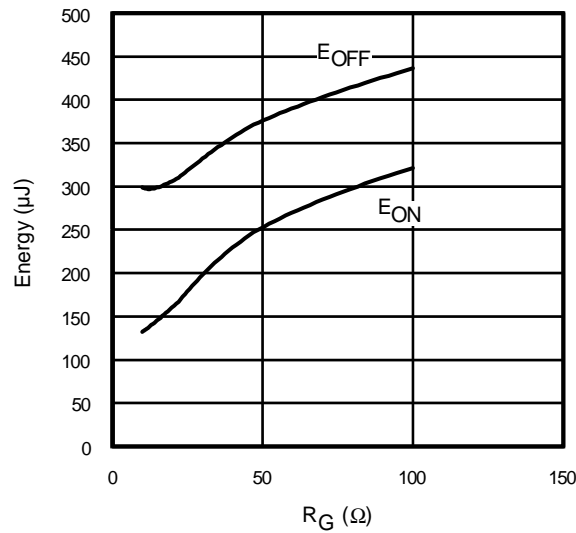
# IRG/B/S/SL10B60KD



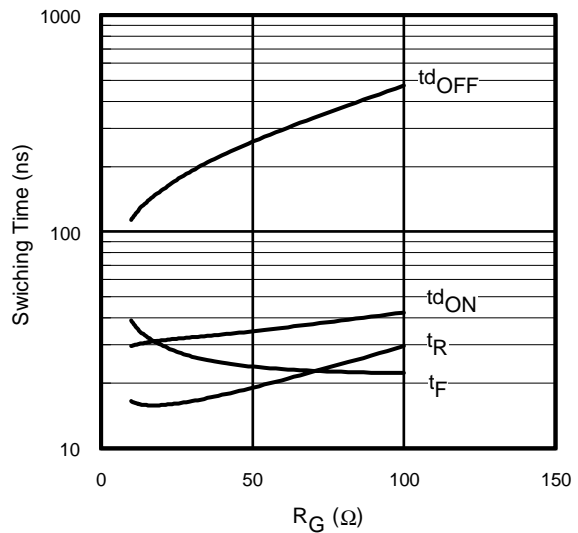
**Fig. 13** - Typ. Energy Loss vs.  $I_C$   
 $T_J = 150^\circ\text{C}$ ;  $L=200\mu\text{H}$ ;  $V_{CE}= 400\text{V}$   
 $R_G= 47\Omega$ ;  $V_{GE}= 15\text{V}$



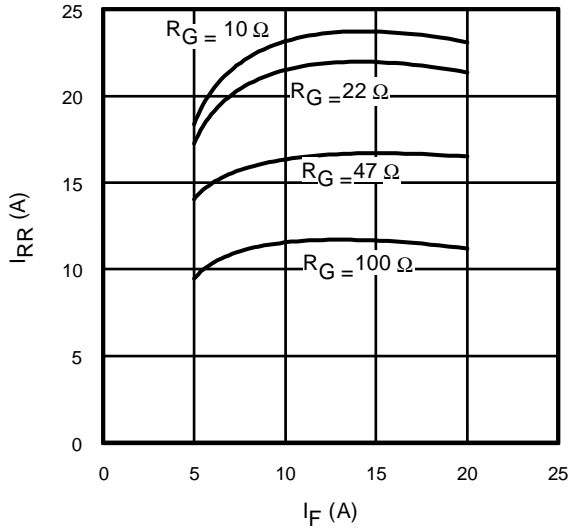
**Fig. 14** - Typ. Switching Time vs.  $I_C$   
 $T_J = 150^\circ\text{C}$ ;  $L=200\mu\text{H}$ ;  $V_{CE}= 400\text{V}$   
 $R_G= 47\Omega$ ;  $V_{GE}= 15\text{V}$



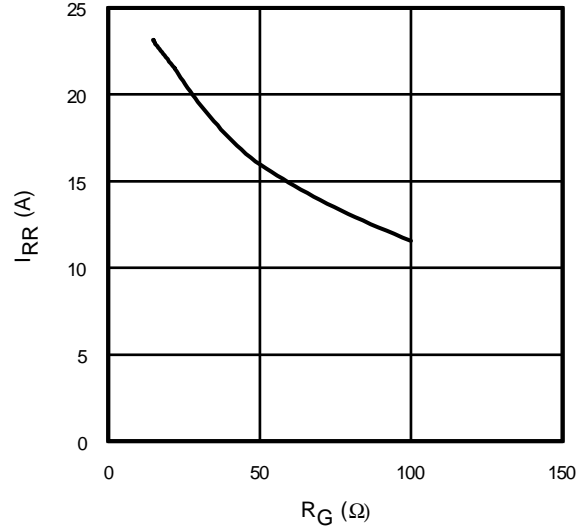
**Fig. 15** - Typ. Energy Loss vs.  $R_G$   
 $T_J = 150^\circ\text{C}$ ;  $L=200\mu\text{H}$ ;  $V_{CE}= 400\text{V}$   
 $I_{CE}= 10\text{A}$ ;  $V_{GE}= 15\text{V}$



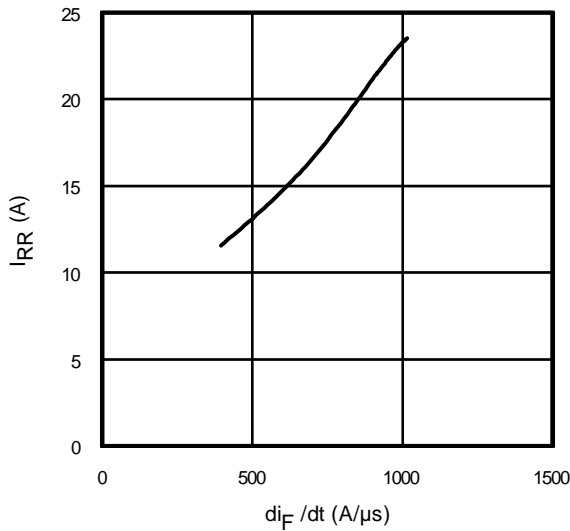
**Fig. 16** - Typ. Switching Time vs.  $R_G$   
 $T_J = 150^\circ\text{C}$ ;  $L=200\mu\text{H}$ ;  $V_{CE}= 400\text{V}$   
 $I_{CE}= 10\text{A}$ ;  $V_{GE}= 15\text{V}$



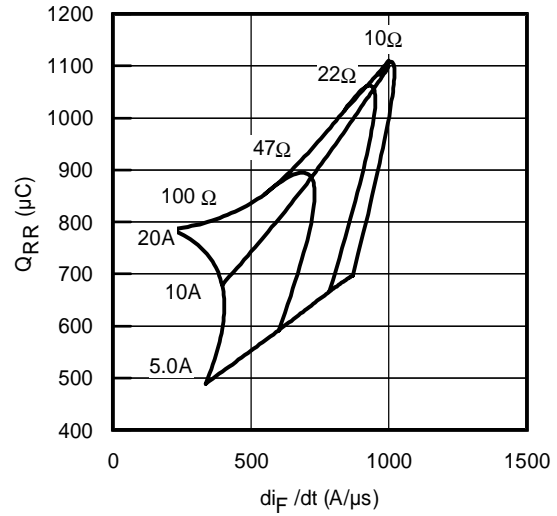
**Fig. 17** - Typical Diode  $I_{RR}$  vs.  $I_F$   
 $T_J = 150^\circ\text{C}$



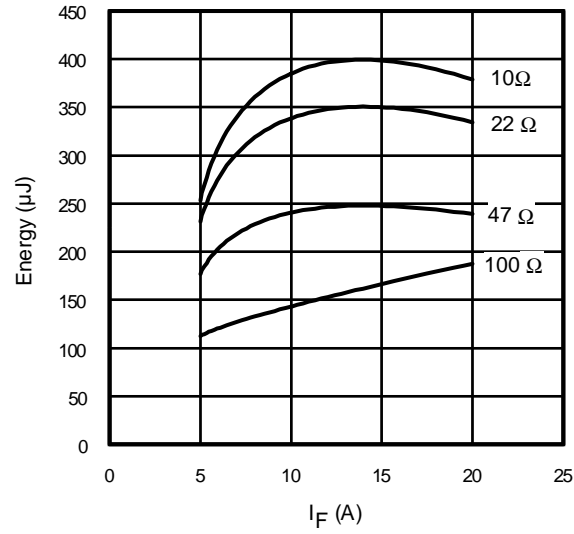
**Fig. 18** - Typical Diode  $I_{RR}$  vs.  $R_G$   
 $T_J = 150^\circ\text{C}; I_F = 10\text{A}$



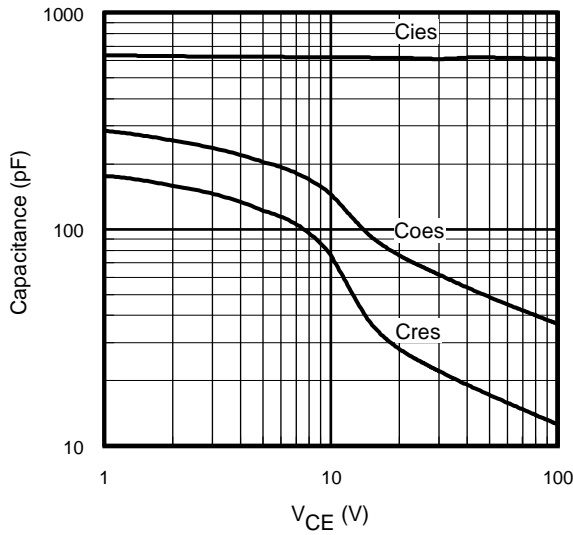
**Fig. 19** - Typical Diode  $I_{RR}$  vs.  $di_F/dt$   
 $V_{CC} = 400\text{V}; V_{GE} = 15\text{V};$   
 $I_{CE} = 10\text{A}; T_J = 150^\circ\text{C}$



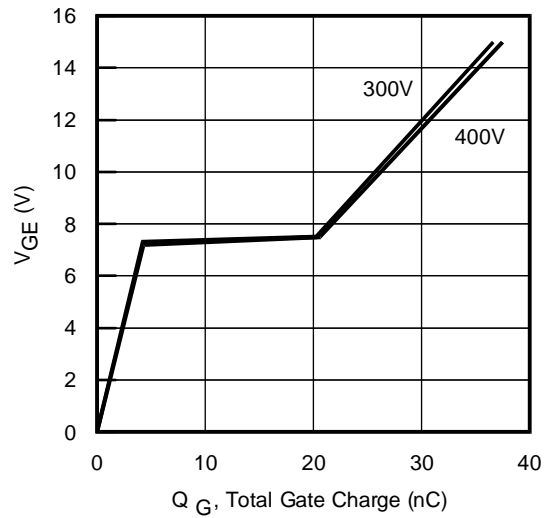
**Fig. 20** - Typical Diode  $Q_{RR}$   
 $V_{CC} = 400\text{V}; V_{GE} = 15\text{V}; T_J = 150^\circ\text{C}$



**Fig. 21** - Typical Diode  $E_{RR}$  vs.  $I_F$   
 $T_J = 150^\circ\text{C}$



**Fig. 22**- Typ. Capacitance vs.  $V_{CE}$   
 $V_{GE} = 0\text{V}$ ;  $f = 1\text{MHz}$



**Fig. 23** - Typical Gate Charge vs.  $V_{GE}$   
 $I_{CE} = 10\text{A}$ ;  $L = 600\ \mu\text{H}$



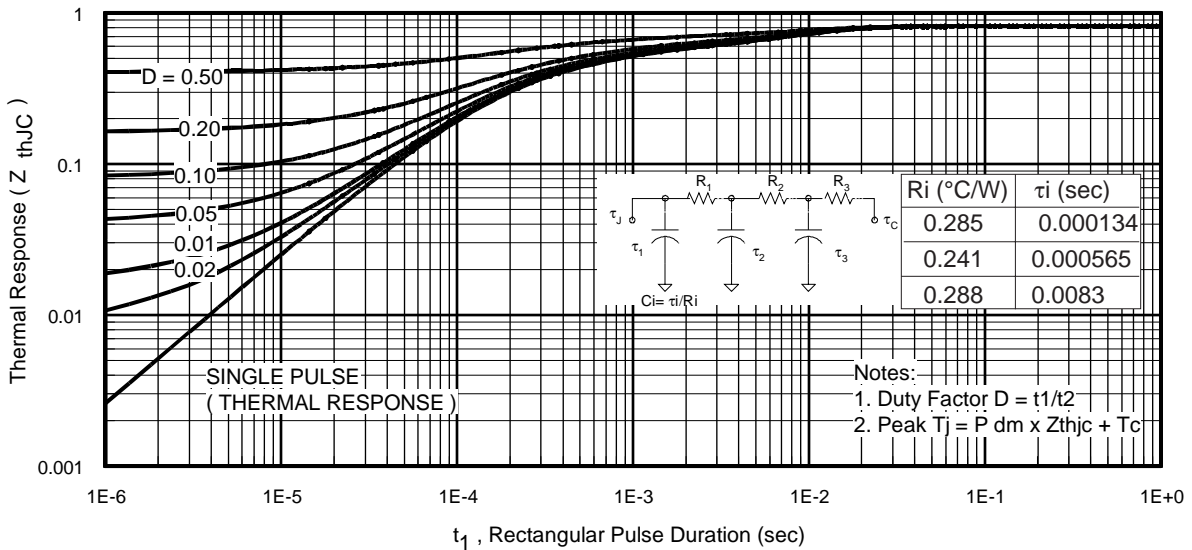


Fig 24. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

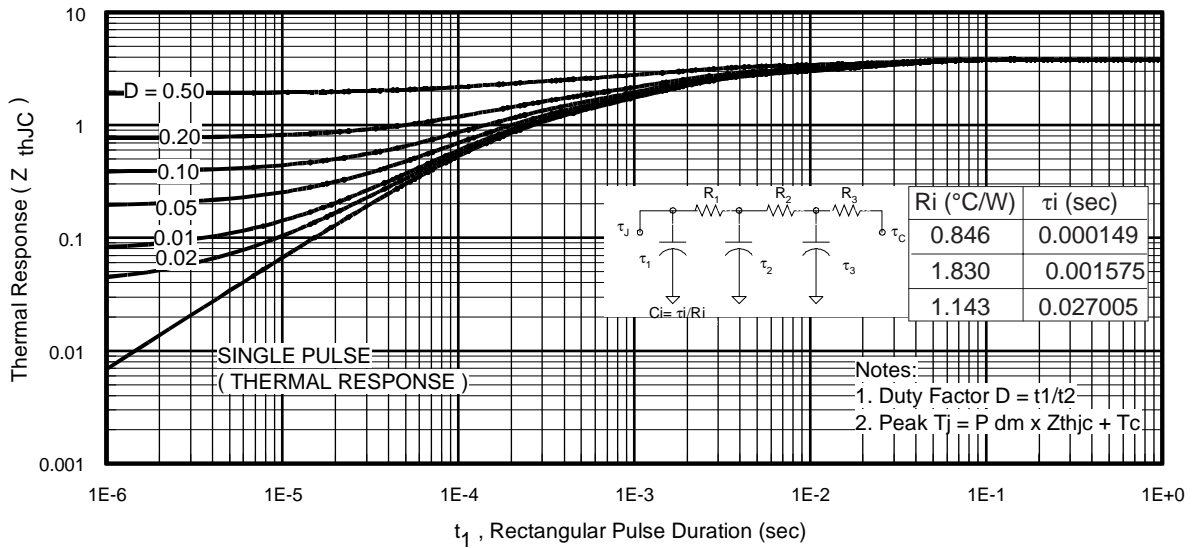
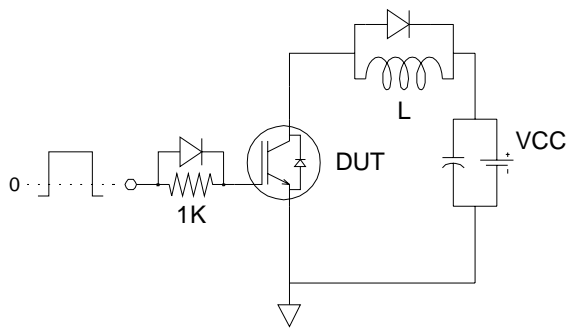


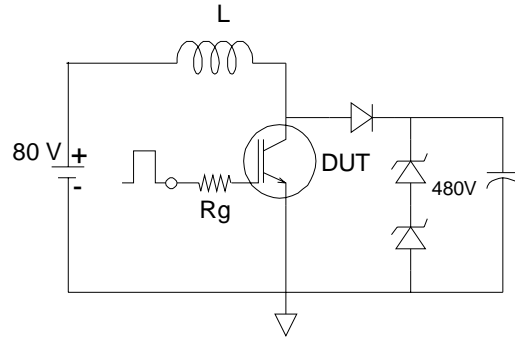
Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

# IRG/B/S/SL10B60KD

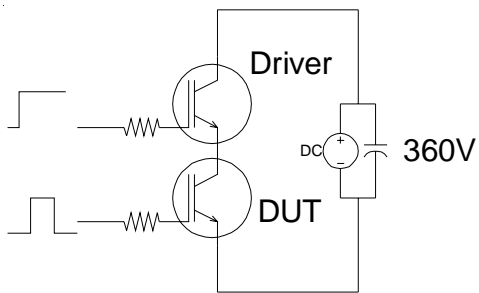
International  
**IR** Rectifier



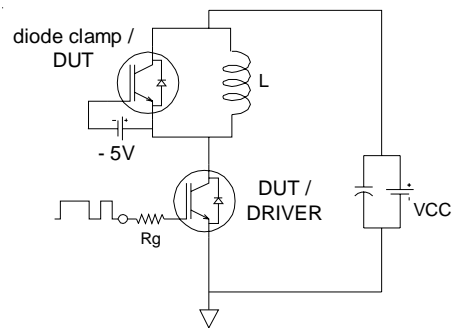
**Fig.C.T.1** - Gate Charge Circuit (turn-off)



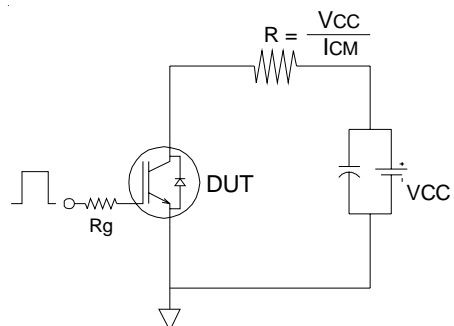
**Fig.C.T.2** - RBSOA Circuit



**Fig.C.T.3** - S.C.SOA Circuit



**Fig.C.T.4** - Switching Loss Circuit



**Fig.C.T.5** - Resistive Load Circuit

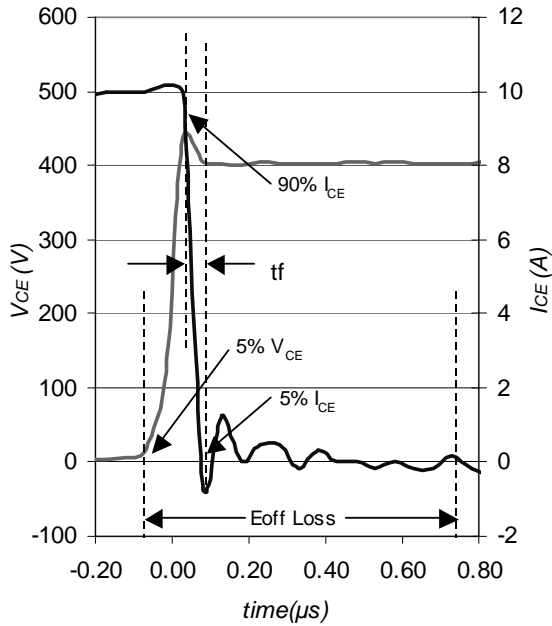


Fig. WF1- Typ. Turn-off Loss Waveform  
@ T<sub>J</sub> = 150°C using Fig. CT.4

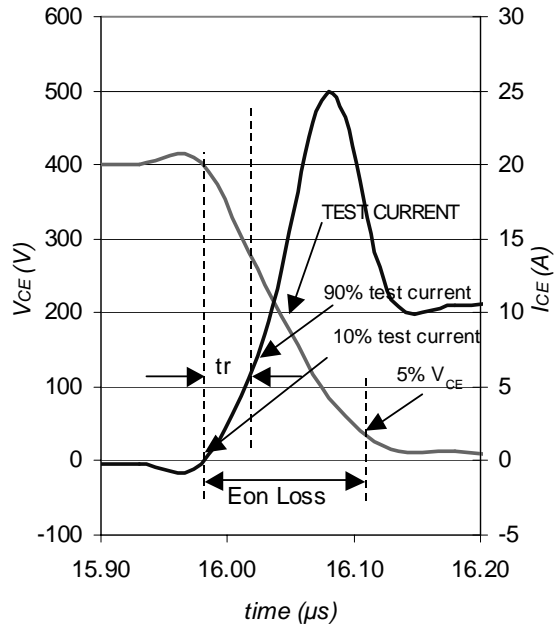


Fig. WF2- Typ. Turn-on Loss Waveform  
@ T<sub>J</sub> = 150°C using Fig. CT.4

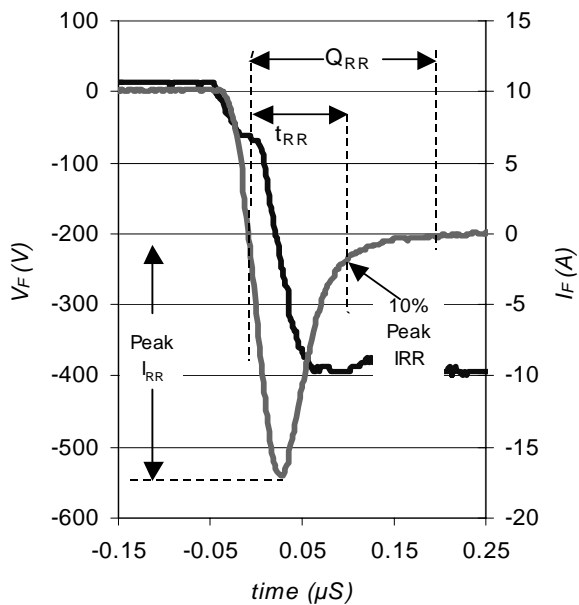


Fig. WF3- Typ. Diode Recovery Waveform  
@ T<sub>J</sub> = 150°C using Fig. CT.4

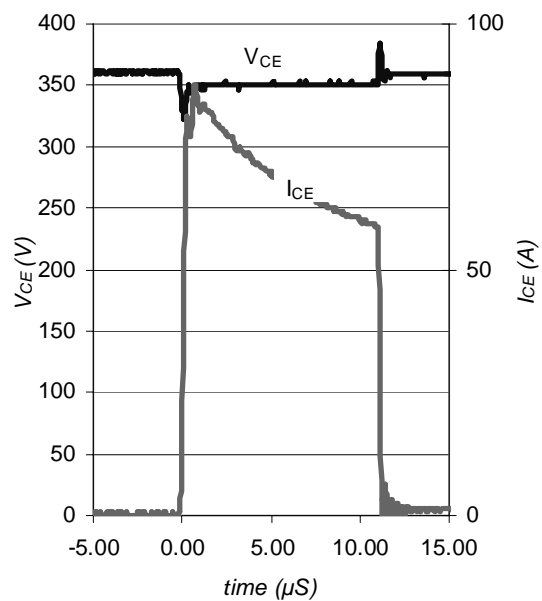


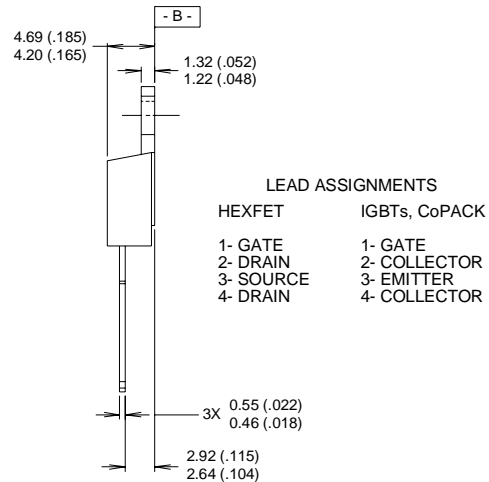
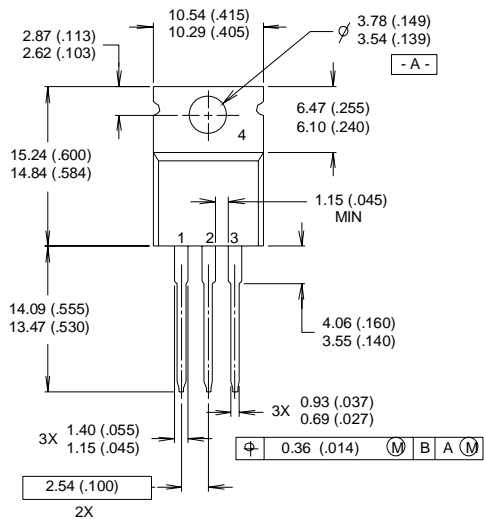
Fig. WF4- Typ. S.C Waveform  
@ T<sub>J</sub> = 150°C using Fig. CT.3

# IRG/B/S/SL10B60KD



## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



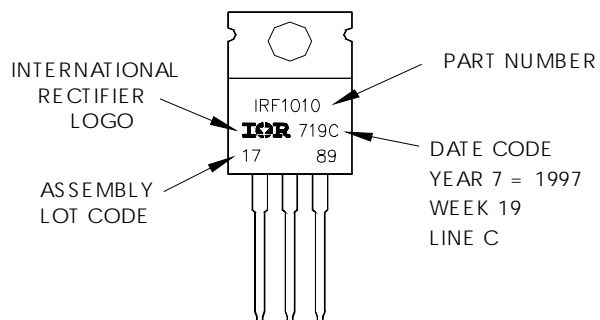
**NOTES:**

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH

- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

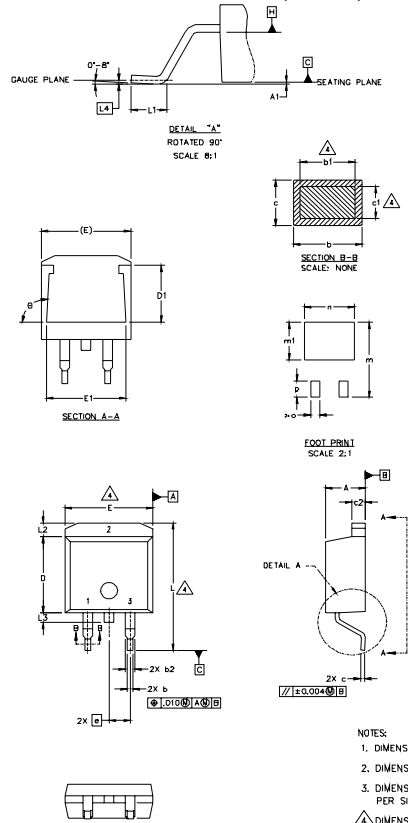
## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"  
**Note:** "P" in assembly line position indicates "Lead-Free"



## D<sup>2</sup>Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1	0.127		.005		
b	0.51	0.99	.020	.039	4
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	3
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

**LEAD ASSIGNMENTS**

HEXFET	IGBTs, CoPACK	DIODES
1- GATE	1- GATE	1- ANODE *
2- DRAIN	2- COLLECTOR	2- CATHODE
3- SOURCE	3- EMITTER	3- ANODE

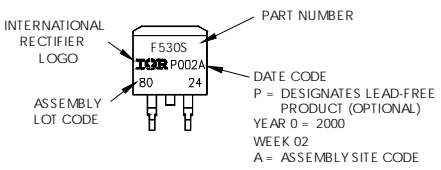
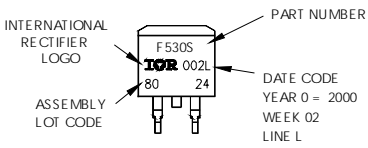
\* PART DEPENDENT.

- NOTES:**
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
  5. CONTROLLING DIMENSION: INCH.

## D<sup>2</sup>Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH  
 LOT CODE 8024  
 ASSEMBLED ON WW 02, 2000  
 IN THE ASSEMBLY LINE "L"

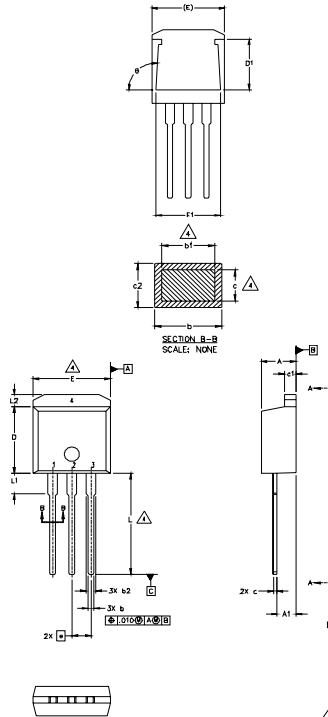
Note: "P" in assembly line position indicates "Lead-Free"



# IRG/B/S/SL10B60KD

## TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	4
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.38	0.63	.015	.025	
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

### LEAD ASSIGNMENTS

#### HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

#### IGBT

- 1 - GATE
- 2 - COLLECTOR
- 3 - EMITTER

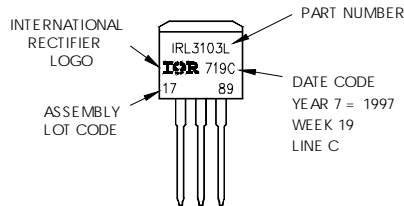
#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

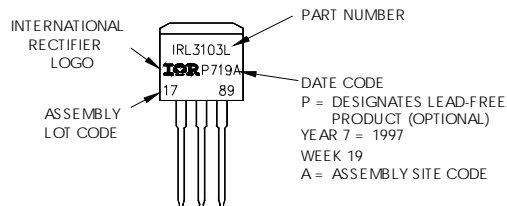
## TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L  
LOT CODE 1789  
ASSEMBLED ON WW 19, 1997  
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"

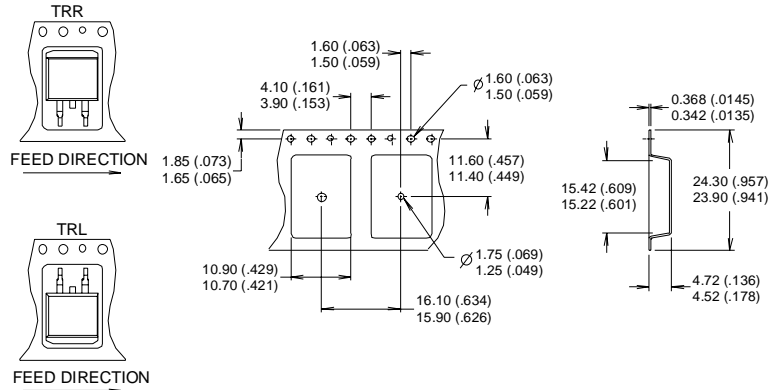


**OR**



## D<sup>2</sup>Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONFORMS TO EIA-418.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION MEASURED @ HUB.
  4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

### Notes:

- ① This is only applied to TO-220AB package
- ② This is applied to D<sup>2</sup>Pak, when mounted on 1" square PCB (FR-4 or G-10 Material).  
For recommended footprint and soldering techniques refer to application note #AN-994.
- ③ Energy losses include "tail" and diode reverse recovery.
- ④  $V_{CC} = 80\% (V_{CES})$ ,  $V_{GE} = 20V$ ,  $L = 100\mu H$ ,  $R_G = 47\Omega$ .

TO-220 package is not recommended for Surface Mount Application

Data and specifications subject to change without notice.  
 This product has been designed and qualified for Industrial market.  
 Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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 TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information. 08/04

Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>